

FORM PTO-1449

Atty. Docket No.:  
B784.312-1Application No.:  
10/017,734LIST OF PATENTS AND PUBLICATIONS FOR  
APPLICANT'S INFORMATION  
DISCLOSURE STATEMENTFirst Named Inventor:  
Baowei KANGFiling Date:  
December 18, 2001Group Art:  
2823

## U.S. PATENT DOCUMENTS

Examiner Initials	Document No.	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Documents
AA			
AB			
AC			
AD			
AE			
AF			
AG			

## FOREIGN PATENT DOCUMENTS

	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Documents	Translation Yes No
AH				
AI				

## OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

KN	AJ	Zohta, Yasuhito et al., "Shallow Donor State Produced by Proton Bombardment of Silicon", <i>Japan J. Appl. Phys.</i> 10, 1971, 532-533.
KN	AK	Gorelinskii, Yu and Nevinnyui, N.N., "Reversible Transformation of Defects in Hydrogen-Implanted Silicon", <i>Nuclear Instruments and Methods</i> 209/210, 1983, 677-682.
KN	AL	Ntsoenzok, E. et al., "Study of the Defects Induced in N-Type Silicon Irradiated by 1-3 MeV Protons", <i>IEEE Transactions of Nuclear Science</i> , Vol. 41, No. 6, December 1994, 1932-1936.
KN	AM	Ntsoenzok, E. et al., "Evolution of Shallow Donors with Proton Fluence in N-Type Silicon", <i>J. appl. Phys.</i> 79(11), June 1, 1996, 8274-8277.
KN	AN	S. Godey et al., "Effect of Shallow Donors Induced by Hydrogen on P+N Junctions", <i>Materials Science &amp; Engineering B58</i> , 1999, 108-112.

EXAMINER:

*Khemraj*

DATE CONSIDERED:

*06/10/04*

EXAMINER: Initial if citation considered whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.